

Comments and Corrections

Correction to “Quantitative Analysis of the Effect of Hydrogen Diffusion From Silicon Oxide Etch-Stopper Layer Into Amorphous In–Ga–Zn–O on Thin-Film Transistor”

Tatsuya Toda, Dapeng Wang, Jingxin Jiang, Mai Phi Hung, and Mamoru Furuta

In the above paper [1], co-author D. Wang’s name was incorrectly spelled in both the biography and the byline. The correct spelling is Dapeng Wang.

REFERENCES

- [1] T. Toda, D. Wang, J. Jiang, M. P. Hung, and M. Furuta, “Quantitative analysis of the effect of hydrogen diffusion from silicon oxide etch-stopper layer into amorphous In–Ga–Zn–O on thin-film transistor,” *IEEE Trans. Electron Devices*, vol. 61, no. 11, pp. 3762–3767, Nov. 2014.